

## Description

The PSJMDP60R1000 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

### MOSFET Product Summary

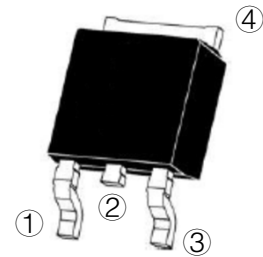
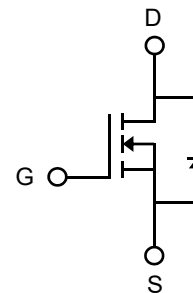
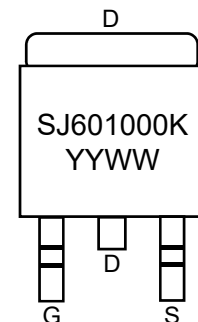
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
600	785 @ $V_{GS} = 10V$	3.3

## Feature

- Fast Switching Capability
- Lead free product is acquired.
- Avalanche Energy Tested

## Applications

- PWM applications
- Load Switch
- Power Management
- DC-DC Converters


**TO-252 (Top View)**

**Circuit Diagram**

**Marking (Top View)**

## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Drain Current-Continuous <sup>1)</sup>	$I_D$	$T_C=25^\circ C$	3.3
		$T_C=100^\circ C$	2.1
Pulsed Drain Current <sup>2)</sup>	$I_{DM}$	7.0	A
Total Power Dissipation <sup>3)</sup>	$P_D$	54.3	W
Avalanche Current <sup>4)</sup>	$I_{AS}$	1.5	A
Avalanche Energy <sup>4)</sup>	$E_{AS}$	21.5	mJ
Thermal Resistance , Junction-to-Case <sup>5)</sup>	$R_{\theta JC}$	2.3	$^\circ C/W$
Thermal Resistance , Junction-to-Ambient <sup>6)</sup>	$R_{\theta JA}$	52	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

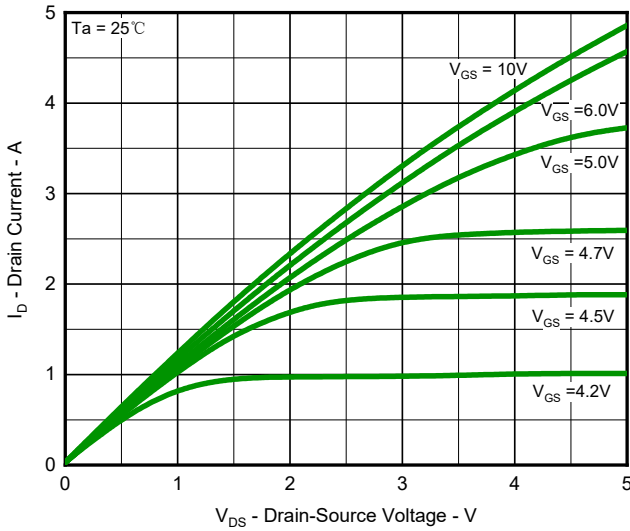
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600	700	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$	-	-	1.0	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	2.9	3.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$	-	785	1008	m $\Omega$
<b>Dynamic Characteristics<sup>7)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	-	232.7	-	pF
Output Capacitance	$C_{oss}$		-	11.5	-	
Reverse Transfer Capacitance	$C_{rss}$		-	0.8	-	
<b>Switching Characteristics<sup>7)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 400V, V_{GS} = 10V,$ $I_D = 1A, R_G = 10\Omega$	-	9.7	-	ns
Turn-on Rise Time	$t_r$		-	8.1	-	
Turn-Off Delay Time	$t_{d(off)}$		-	29.3	-	
Turn-Off Fall Time	$t_f$		-	34.5	-	
Total Gate Charge	$Q_g$	$V_{DS} = 480V, V_{GS} = 10V,$ $I_D = 1A$	-	6.4	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.1	-	
Gate-Drain Charge	$Q_{gd}$		-	2.5	-	
Gate Resistance	$R_g$	$f=1MHz$ , Open Drain	-	5.6	-	$\Omega$
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 1A$	-	0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 1A, V_R = 200V,$ $dI_F/dt = 100A/\mu s$	-	102	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	430.7	-	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		-	8.45	-	A

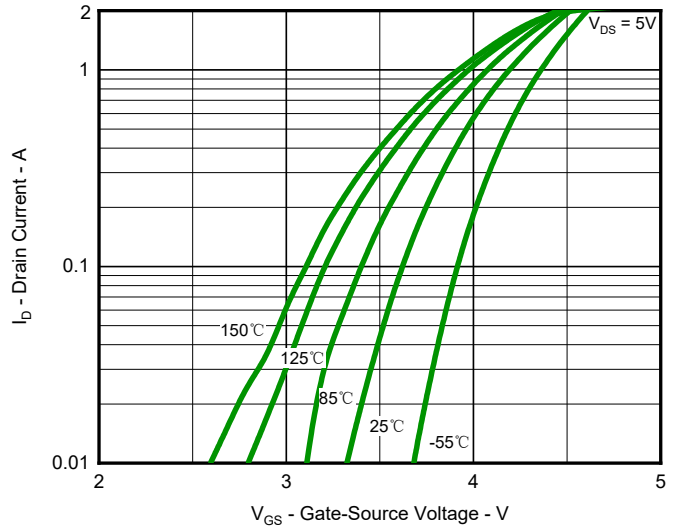
## Notes:

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature( $T_{J\_Max}=150^\circ C$ ).
3. Pulse Test: Pulse Width  $\leq 10\mu s$ , Duty Cycle  $\leq 1\%$ .
4. This single-pulse measurement was taken under the following condition [ $L=20mH, V_{GS}=10V, V_{DS}=100V$ ]while it's value is limited by  $T_{J\_Max}=150^\circ C$ .
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on infinite heatsink.
7. Guaranteed by design, not subject to production.

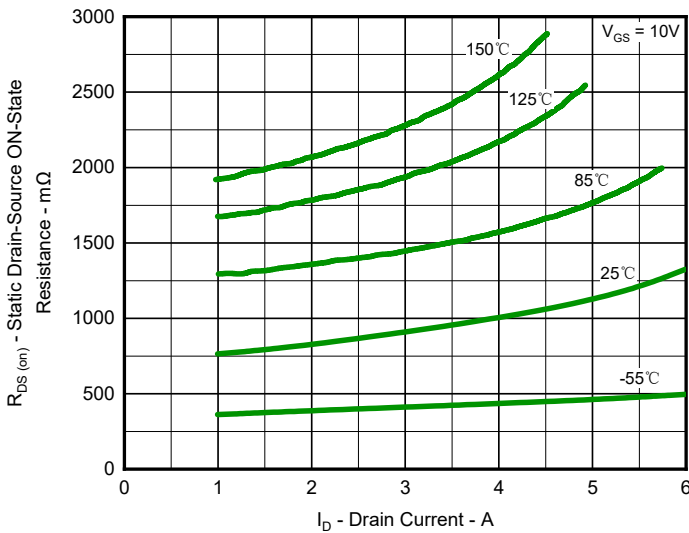
## Typical Characteristics



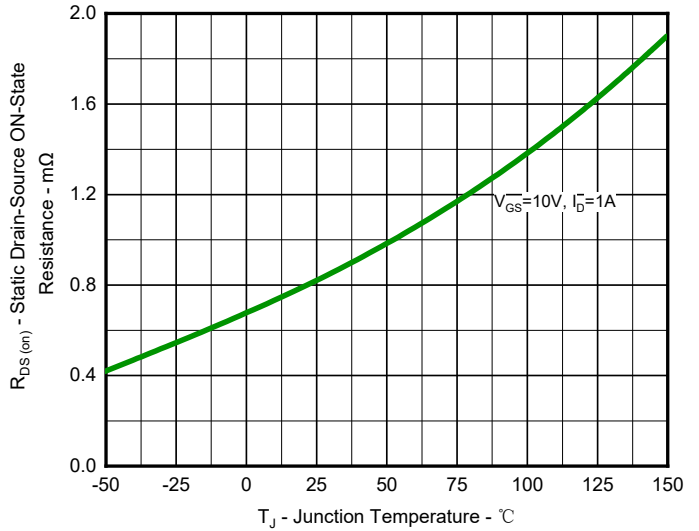
**Fig.1 Output Characteristics**



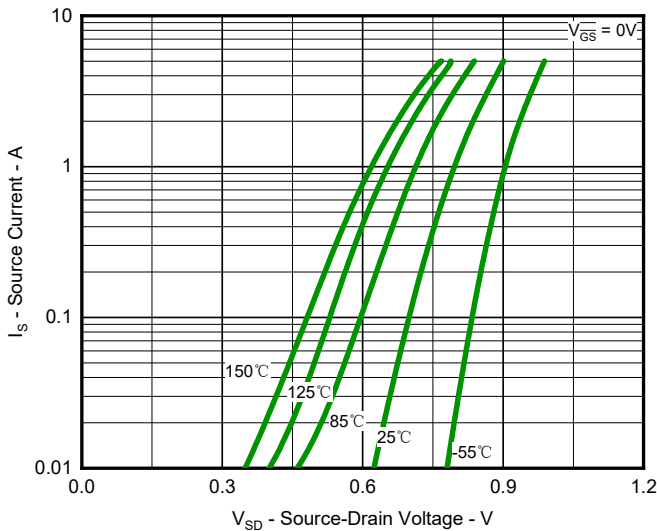
**Fig.2 Typical Transfer Characteristic**



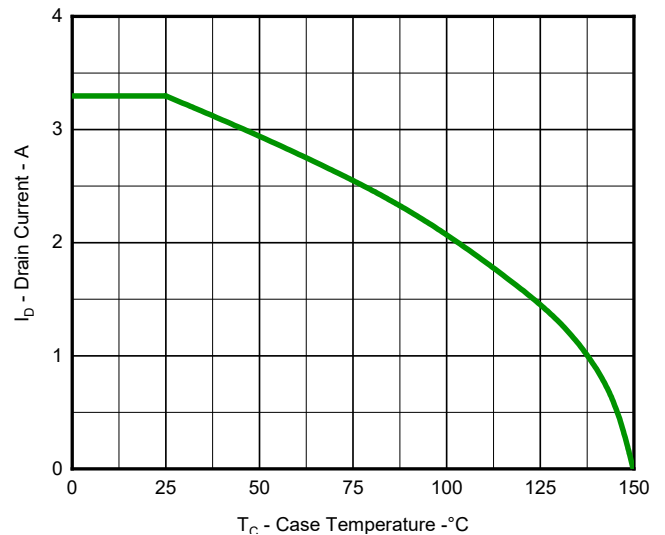
**Fig.3 Typical On-Resistance vs Drain Current and Temperature**



**Fig.4 On-Resistance Variation with Temperature**



**Fig.5 Diode Forward Voltage vs. Current**



**Fig.6 Maximum Drain Current vs. Case Temperature**

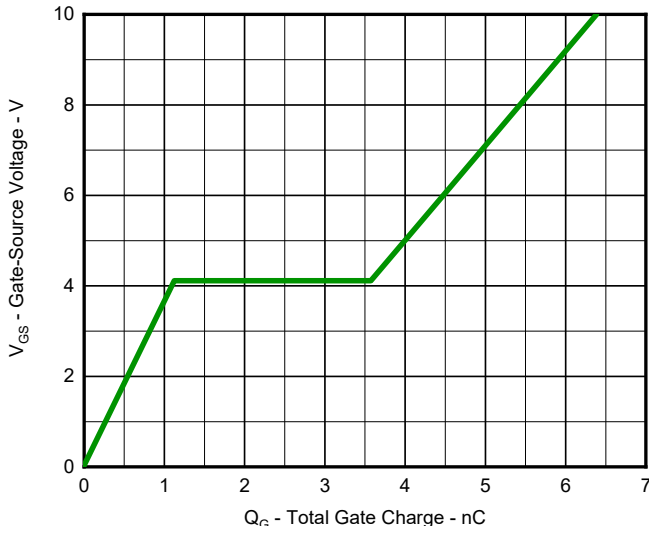


Fig.7 Gate Charge Characteristics

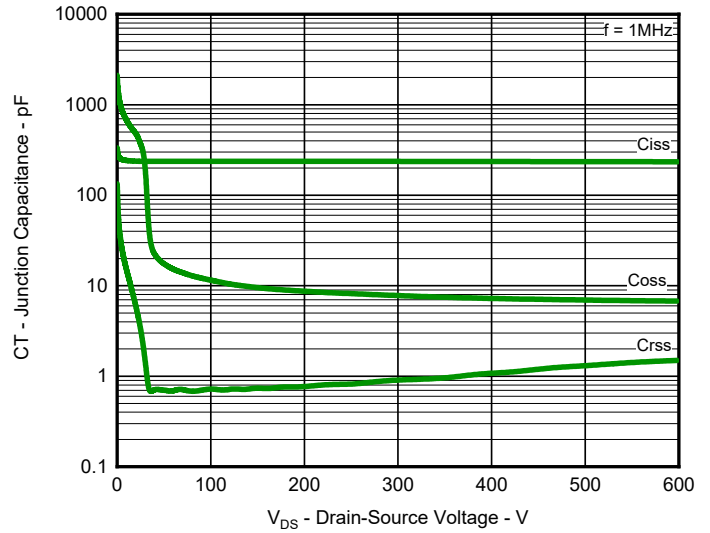


Fig.8 Typical Junction Capacitance

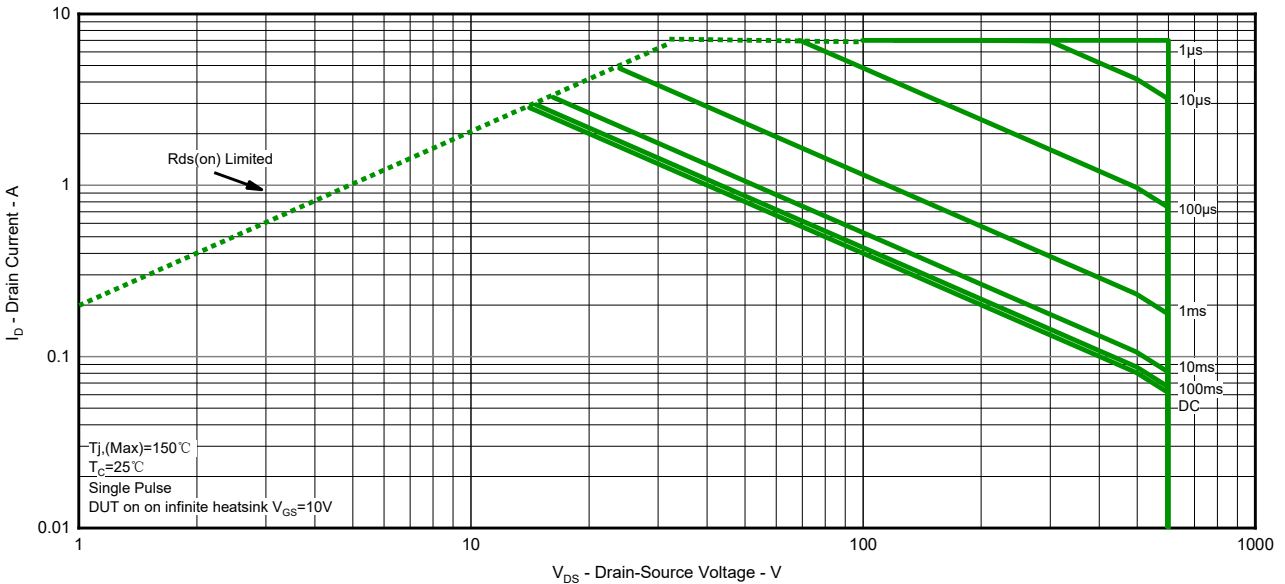


Fig.9 Safe Operation Area

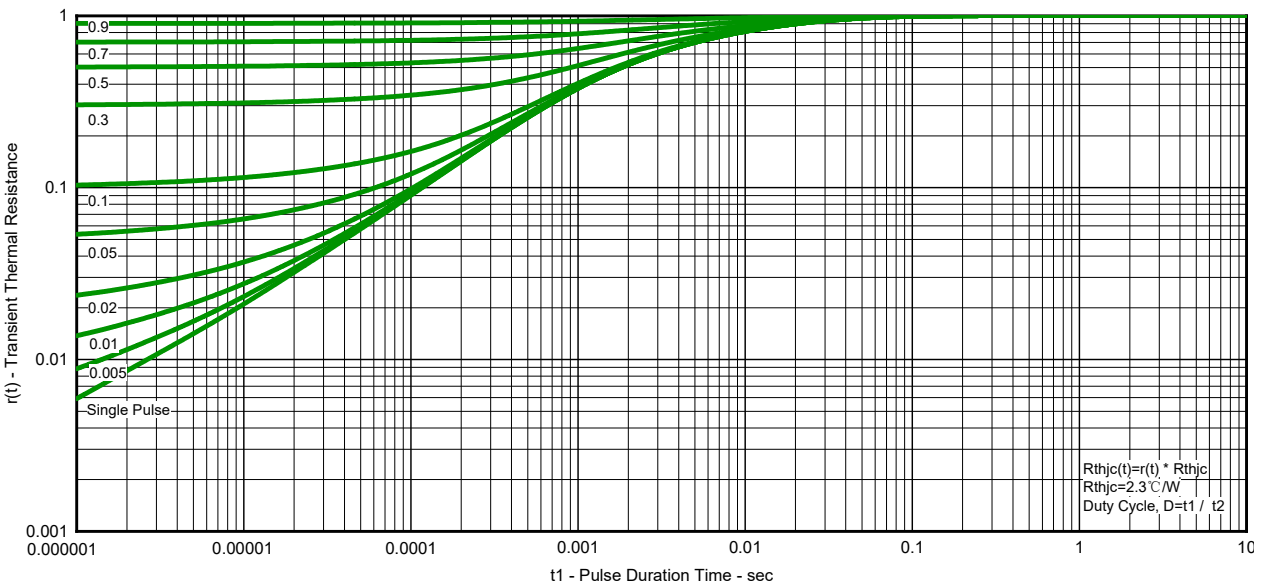
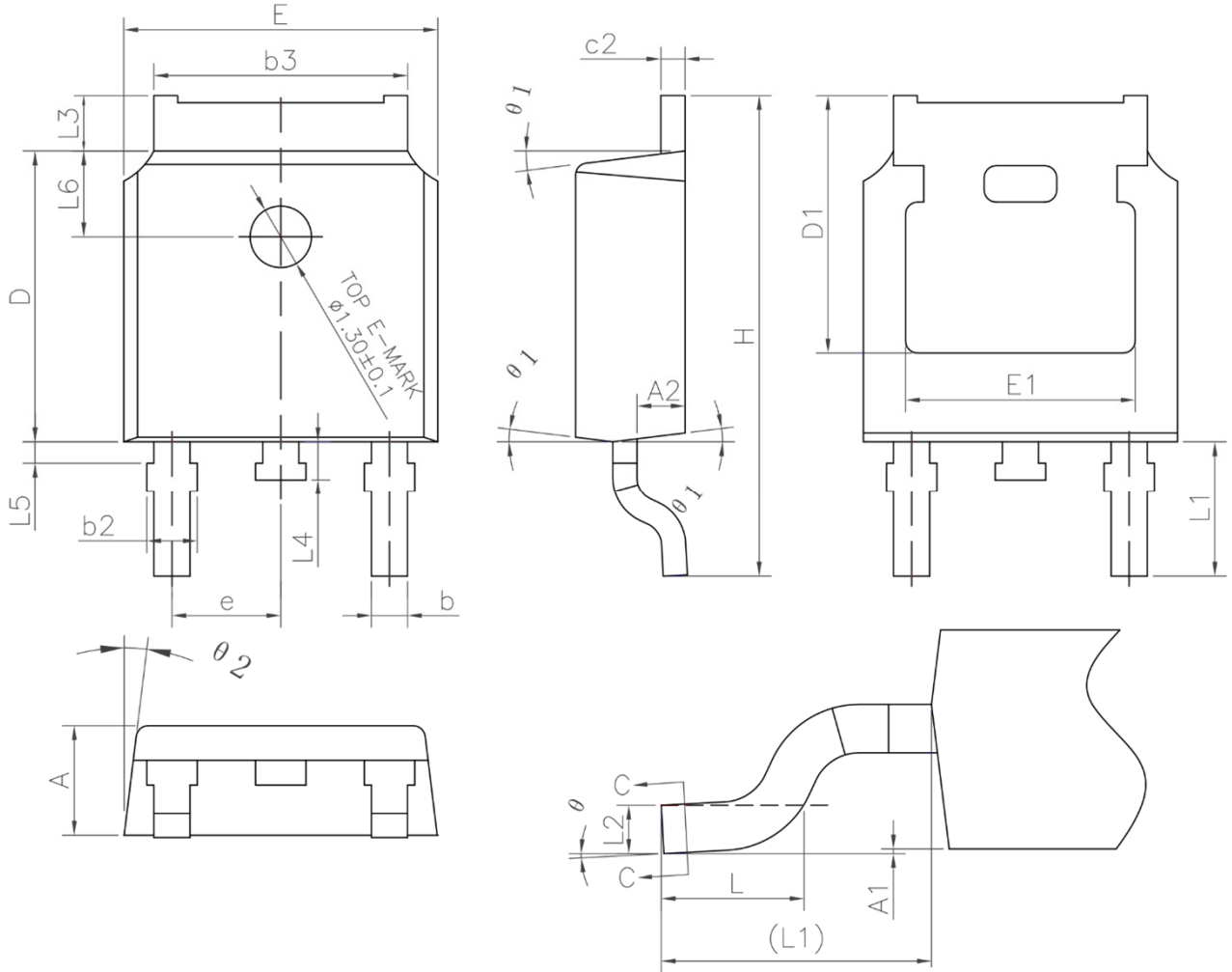


Fig.10 Transient Thermal Resistance

## Product Dimension (TO-252)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	2.20	2.38	0.087	0.094	e	2.186	2.386	0.086	0.094
A1	0.00	0.10	0.000	0.004	H	9.80	10.40	0.386	0.409
A2	0.90	1.10	0.035	0.043	L	1.40	1.70	0.055	0.067
b	0.72	0.82	0.028	0.032	L1	2.90 Ref.		0.114 Ref.	
b2	0.72	0.90	0.028	0.035	L2	0.508 BSC.		0.020 BSC.	
b3	5.13	5.46	0.202	0.215	L3	0.90	1.25	0.035	0.049
c	0.47	0.60	0.019	0.024	L4	0.60	1.00	0.024	0.039
c2	0.47	0.60	0.019	0.024	L5	0.15	0.75	0.006	0.030
D	6.00	6.20	0.236	0.244	L6	1.80 Ref.		0.071 Ref.	
D1	5.25	-	0.207	-	θ	0°	8°	0°	8°
E	6.50	6.70	0.256	0.264	θ1	5°	9°	5°	9°
E1	4.70	-	0.185	-	θ2	5°	9°	5°	9°

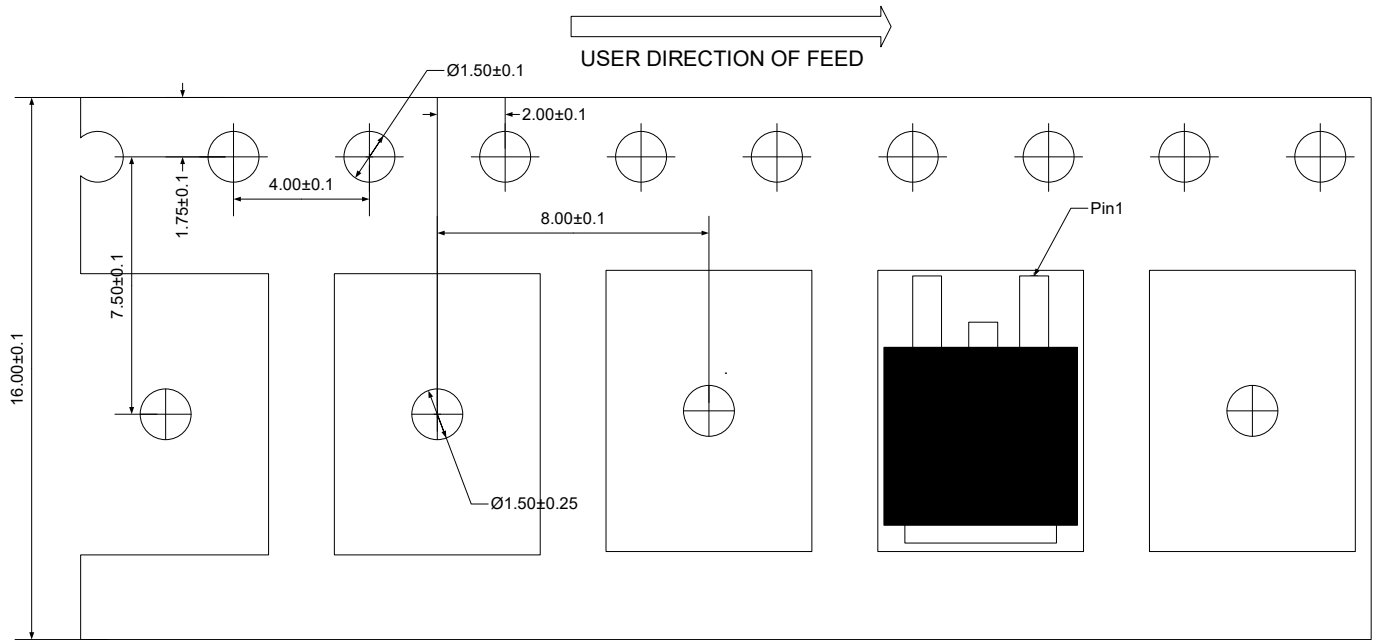
# N-Channel MOSFET

# PSJMDP60R1000

## Ordering Information

Device	Package	Reel	Shipping
PSJMDP60R1000	TO-252	13"	2500 / Tape & Reel

## Load With Information



Unit:mm

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